

Sixth Semester B.E. Degree Examination, June/July 2018
Microelectronic Circuits

Time: 3 hrs.

Max. Marks:100

**Note: Answer any THREE full questions from Part-A
and any TWO full questions from Part-B.**

PART - A

- 1 a. Discuss the VI characteristics of the n-MOSFET in different regions by deriving $i_D - V_{DS}$ relationship equation. (12 Marks)
- b. Consider the circuit given in Fig.Q1(b). Let the voltage V_D be applied to the gate of another transistor for Q_2 as shown in Fig.Q1(b). Assume Q_1 and Q_2 are identical and $\lambda = 0$. Find the drain current and voltage of Q_2 and R at Q_1 . Let $V_{DD} = 5V$, $V_t = 0.6V$, $\mu_n C_{ox} = 200 \mu A/V^2$, $L = 0.8 \mu m$, $w = 4 \mu m$, $V_{OV} = 0.4 V$. (08 Marks)

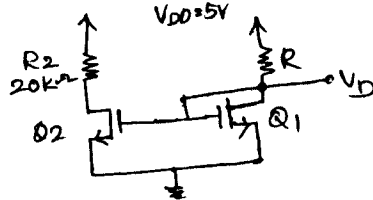


Fig.Q1(b)

- 2 a. Characterize the common source single stage amplifier with and without source degeneration circuit by deriving the amplifier parameters of R_{in} , V_i , V_o , A_v , A_{vO} , R_{out} and G_{vO} . (10 Marks)
- b. Consider the circuit given in below Fig.Q2(b) to establish a dc current of $I_D = 0.5 \text{ mA}$. The MOSFET is specified to have $V_t = 1 \text{ V}$, $K'W/L = 1 \text{ mA/V}^2$. Let $\lambda = 0$, $V_{DD} = 15V$. If instead of given circuit fixed - V_{gs} bias circuit is used then find the value of required V_{gs} to establish $I_D = 0.5 \text{ mA}$. Calculate in both the type of biasing circuits the percentage change in the value of I_D obtained when MOSFET is replaced with another unit having the same $K(W/L)$ but $V_t = 1.5V$. [Hint : Choose R_D and R_S to provide $1/3$ of V_{DD} as a drop across them]. (10 Marks)

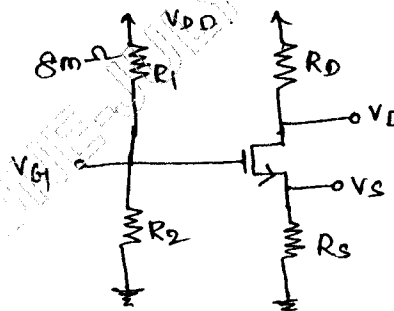


Fig.Q2(b)

- 3 a. What do you understand about current steering process? Draw and explain a BJT current steering circuit to generate number of constant currents of various magnitudes. (07 Marks)
- b. What are the different short channel effects? (05 Marks)

- c. For the given circuit in Fig.Q3(c) find the width of all the transistors. Let $V_{DD} = V_{SS} = 3V$, $V_{tn} = 0.6V$, $V_{tp} = -0.6V$, and all the channel length $L = 1 \mu m$, $K_n = 200 \mu A/V^2$, $K_p = 80 \mu A/V^2$, $I_{ref} = 10 \mu A$, $I_2 = 80 \mu A$, $I_3 = 40 \mu A$, $I_5 = 70 \mu A$, and $\lambda = 0$. The required voltage at the drain of Q_2 allowed to go down to within 0.3V of negative supply and that the voltage at the drain of Q_5 be allowed to go upto 0.2 V of the positive supply. (08 Marks)

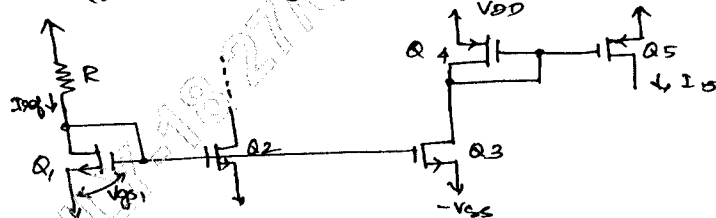


Fig.Q3(c)

- 4 a. Draw the circuit of common gate amplifier with its active loads. Discuss the small signal analysis and high frequency response. (10 Marks)
 b. What are two different parameters that decides the performance of the current mirror. Explain the BJT Wilson current mirror circuit and compare it with cascode current mirror. (06 Marks)
 c. Design Widler current source circuit for generating a constant current $I_o = 10 \mu A$ which operate from a 10V supply. Determine the values of the required resistors assuming V_{BE} is 0.7 V at a current of 1 mA and neglecting the effect of finite β . (04 Marks)
- 5 a. Draw the circuit diagram and different stages of two stage CMOS op-amp and explain its structure with all its parameters. (10 Marks)
 b. Discuss the large signal and small signal operation of the MOS differential pair. (10 Marks)

PART - B

- 6 a. Explain the different amplifiers to describe the four different feedback topologies. (10 Marks)
 b. What do you understand about the frequency compensation method of an amplifier to maintain stability for desired value of gain? (10 Marks)
- 7 a. What are the different non-linear functional op-amp circuits? Explain them by deriving the expression for its output voltage. (10 Marks)
 b. What are the limitations on the performance of op-amp circuits at large o/p signals? (07 Marks)
 c. Design an inverting amplifier using op-amp having a gain of -10 and input resistance of $100 k\Omega$. (03 Marks)
- 8 a. Implement the CMOS logic circuit for the expression $y = A + B(C + DE)$. Provide the W/L ratios of all n-transistor in your circuit, with proper transistor sizing. Assume that for the basic inverter $n = 2$ and $p = 5$ and that the channel length is $0.18 \mu m$. (08 Marks)
 b. Design a level restored n-pass transistor logic circuit for the given expression $Y = A + BC$. Explain the concept of level restoration using your own circuit. (06 Marks)
 c. Consider a CMOS inverter fabricated in a $0.25 \mu m$ process for which $C_{ox} = 6 fF/\mu m^2$, $\mu_n C_{cx} = 115 \mu A/V^2$, $\mu_p C_{ox} = 30 \mu A/V^2$, $V_{th} = -V_{tp} = 0.4 V$ and $V_{DD} = 2.5 V$. The W/L ratio of Q_N is $\frac{0.375 \mu m}{0.25 \mu m}$, and that for Q_p is $\frac{1.125 \mu m}{0.25 \mu m}$. The gate-source and gate-drain overlap capacitances are specified to be $0.3 fF/\mu m$ of gate width. Further the effective value of drain body capacitances are $C_{dbn} = 1 fF$ and $C_{dbp} = 1 fF$. The wiring capacitance $C_w = 0.2 fF$. Find propagation delay t_p . (06 Marks)
